

Insulated Gate Bipolar Transistor (Warp 2 Speed IGBT), 90 A


SOT-227
FEATURES

- NPT warp 2 speed IGBT technology with positive temperature coefficient
- Square RBSOA
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery
- Fully isolated package
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRODUCT SUMMARY	
V_{CES}	600 V
I_C DC	90 A at 90 °C
$V_{CE(on)}$ typical at 100 A, 25 °C	2.40 V
I_F DC	108 A at 90 °C

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Higher switching frequency up to 150 kHz
- Lower conduction losses and switching losses
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V_{CES}		600	V	
Continuous collector current	I_C	$T_C = 25\text{ °C}$	147	A	
		$T_C = 90\text{ °C}$	90		
Pulsed collector current	I_{CM}		300		
Clamped inductive load current	I_{LM}		300		
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	180		
		$T_C = 90\text{ °C}$	108		
Gate-to-emitter voltage	V_{GE}		± 20	V	
Power dissipation, IGBT	P_D	$T_C = 25\text{ °C}$	625	W	
		$T_C = 90\text{ °C}$	300		
Power dissipation, diode	P_D	$T_C = 25\text{ °C}$	379		
		$T_C = 90\text{ °C}$	182		
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500		V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	-	-	
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$	-	2.4	2.8	V
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	3	3.4	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	3.3	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	3	3.9	5.0	
		$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}, T_J = 125\text{ }^\circ\text{C}$	-	2.5	-	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$ (25 °C to 125 °C)	-	- 10	-	mV/°C
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	-	7	100	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.5	6.0	mA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	6	10	
Forward voltage drop, diode	V_{FM}	$I_C = 100\text{ A}, V_{GE} = 0\text{ V}$	-	1.6	2.1	V
		$I_C = 100\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.56	2.0	
		$I_C = 100\text{ A}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	1.53	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Total gate charge (turn-on)	Q_g	$I_C = 100\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}$	-	460	690	nC		
Gate to emitter charge (turn-on)	Q_{ge}		-	160	250			
Gate to collector charge (turn-on)	Q_{gc}		-	70	130			
Turn-on switching loss	E_{on}	$I_C = 100\text{ A}, V_{CC} = 360\text{ V}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$	-	0.39	-	mJ		
Turn-off switching loss	E_{off}		-	1.10	-			
Total switching loss	E_{tot}		-	1.49	-			
Turn-on delay time	$t_{d(on)}$		Energy losses include tail and diode recovery. Diode used 60APH06	-	245	-	ns	
Rise time	t_r			-	53	-		
Turn-off delay time	$t_{d(off)}$			-	240	-		
Fall time	t_f			-	63	-		
Turn-on switching loss	E_{on}			$I_C = 100\text{ A}, V_{CC} = 360\text{ V}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	0.52	-	mJ
Turn-off switching loss	E_{off}				-	1.24	-	
Total switching loss	E_{tot}				-	1.76	-	
Turn-on delay time	$t_{d(on)}$	-	240		-	ns		
Rise time	t_r	-	54		-			
Turn-off delay time	$t_{d(off)}$	-	250	-				
Fall time	t_f	-	80	-				
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 300\text{ A}, R_g = 22\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 400\text{ V}, V_P = 600\text{ V}, L = 500\text{ }\mu\text{H}$	Fullsquare					
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}$	-	95	-	ns		
Diode peak reverse current	I_{rr}		-	10	-	A		
Diode recovery charge	Q_{rr}		-	480	-	nC		
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	144	-	ns		
Diode peak reverse current	I_{rr}		-	16	-	A		
Diode recovery charge	Q_{rr}		-	1136	-	nC		



THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature	T_J, T_{Stg}	- 40	-	150	$^{\circ}C$
Junction to case	IGBT	-	-	0.20	$^{\circ}C/W$
	Diode	-	-	0.33	
Case to sink thermal resistance, flat greased surface	R_{thCS}	-	0.1	-	
Mounting torque, on terminals and heatsink	T	-	-	1.3	Nm
Weight		-	30	-	g
Case style		SOT-227			

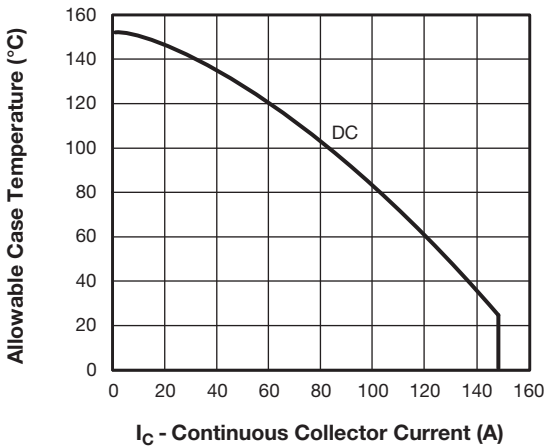


Fig. 1 - Maximum DC IGBT Collector Current vs. Case Temperature

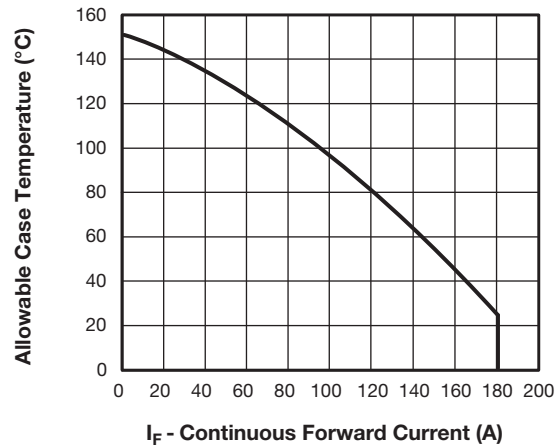


Fig. 3 - Maximum Allowable Forward Current vs. Case Temperature, Diode Leg

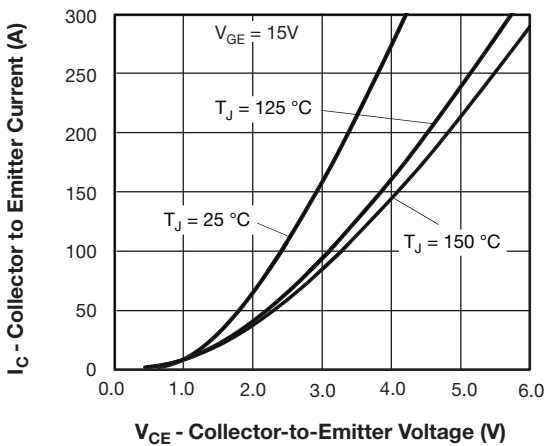


Fig. 2 - Typical Collector to Emitter Voltage (V)

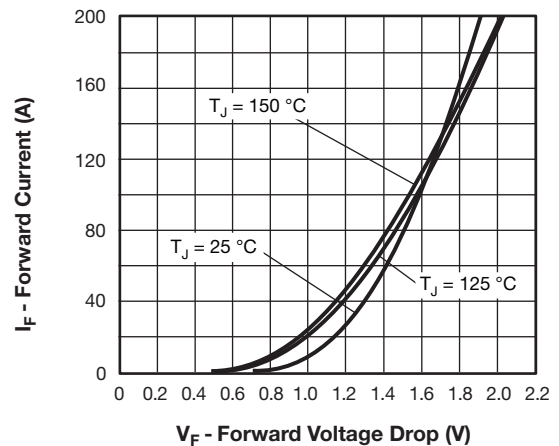


Fig. 4 - Typical Forward Voltage Drop Characteristics

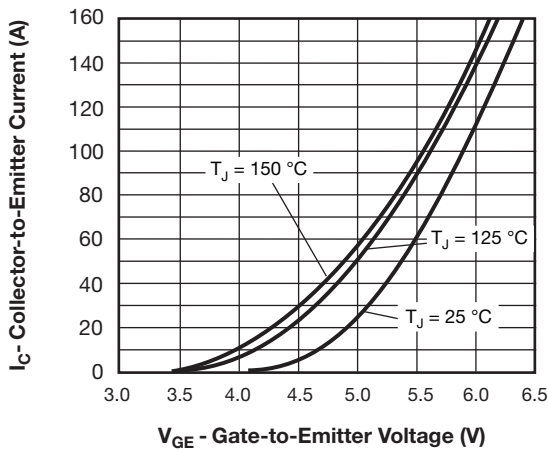


Fig. 5 - Typical IGBT Transfer Characteristics

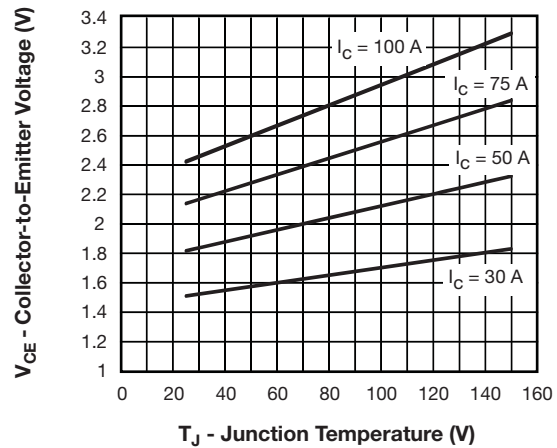


Fig. 8 - Typical IGBT Collector to Emitter Voltage vs. Junction Temperature, $V_{GE} = 15\text{ V}$

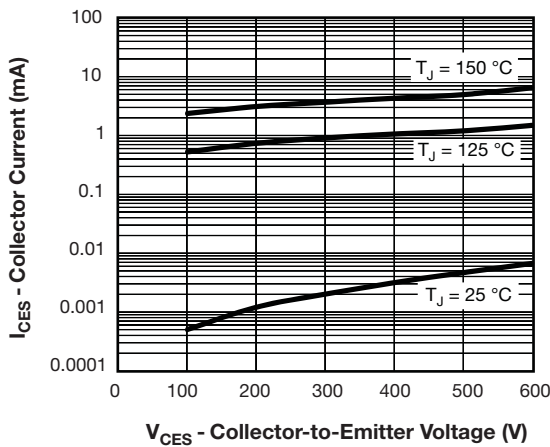


Fig. 6 - Typical IGBT Zero Gate Voltage Collector Current

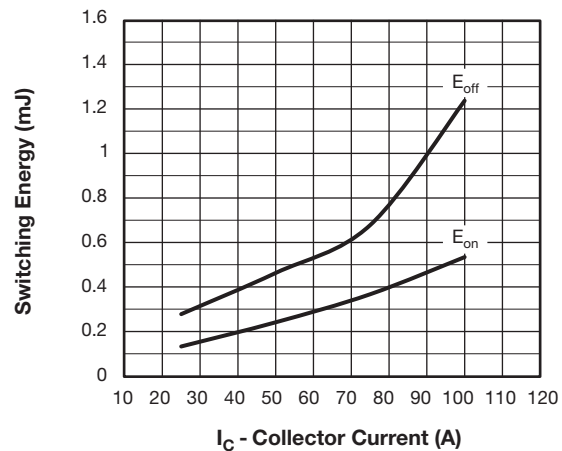


Fig. 9 - Typical IGBT Energy Losses vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 360\text{ V}$,
 $R_g = 5\text{ }\Omega$, $V_{GE} = 15\text{ V}$, Diode used: 60APH06

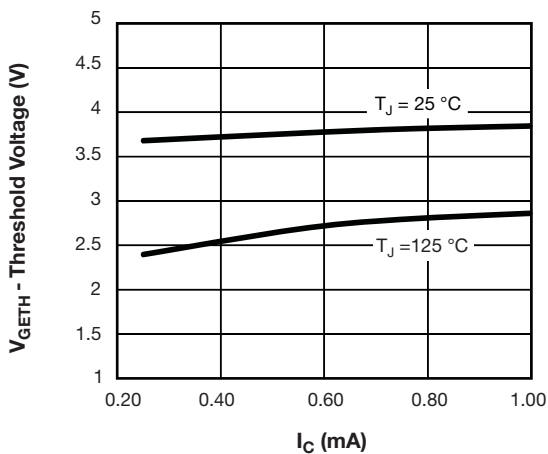


Fig. 7 - Typical IGBT Threshold Voltage

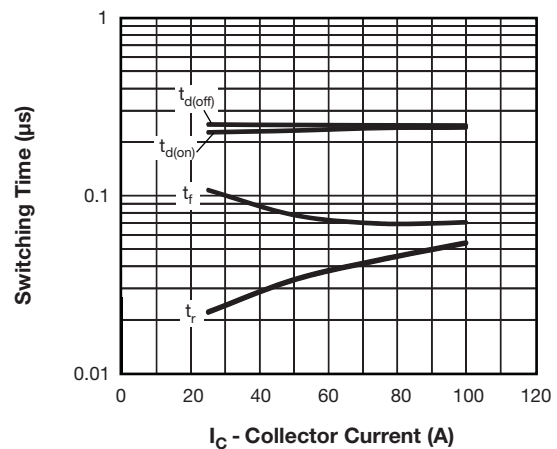


Fig. 10 - Typical IGBT Switching Time vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 360\text{ V}$,
 $R_g = 5\text{ }\Omega$, $V_{GE} = 15\text{ V}$, Diode used: 60APH06

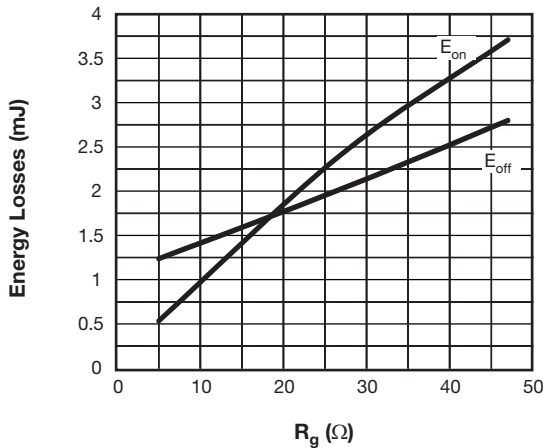


Fig. 11 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $I_C = 100\text{ A}$, $L = 500\text{ }\mu\text{H}$,
 $V_{CC} = 360\text{ V}$, $V_{GE} = 15\text{ V}$, Diode used: 60APH06

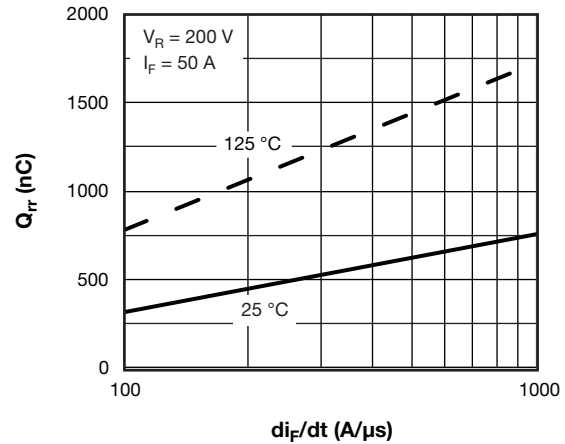


Fig. 14 - Typical Stored Charge vs. di_F/dt of Diode

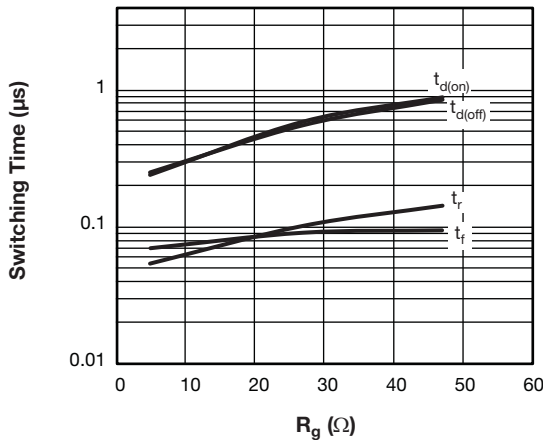


Fig. 12 - Typical IGBT Switching Time vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 360\text{ V}$,
 $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, Diode used: 60APH06

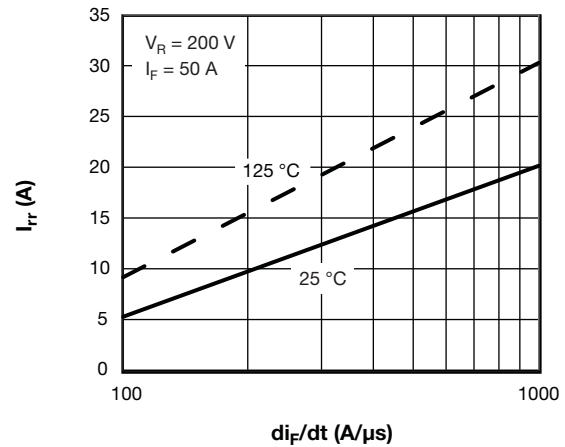


Fig. 15 - Typical Reverse Recovery Current vs. di_F/dt of Diode

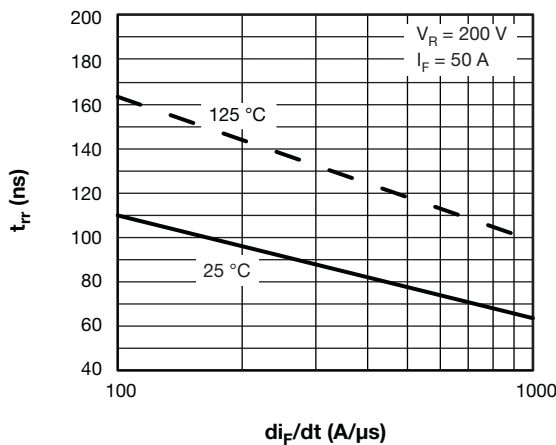


Fig. 13 - Typical Reverse Recovery Time vs. di_F/dt , of Diode

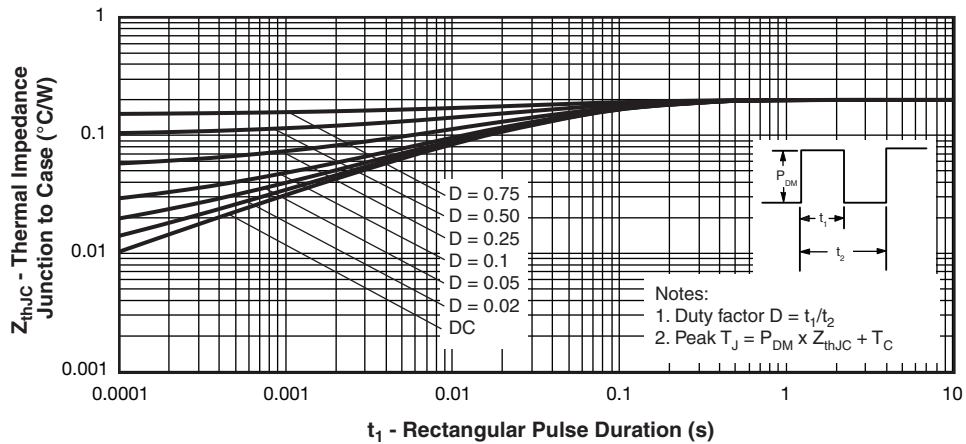


Fig. 16 - Maximum Thermal Impedance Z_{thJC} Characteristics, IGBT

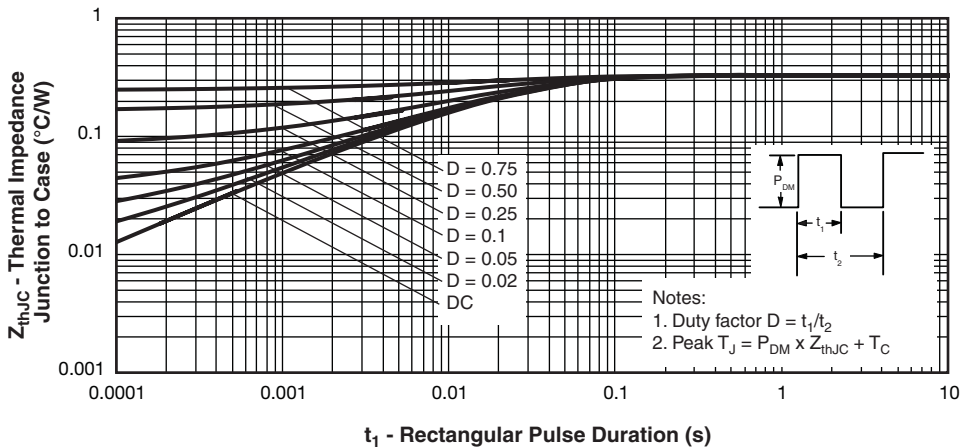


Fig. 17 - Maximum Thermal Impedance Z_{thJC} Characteristics, Diode

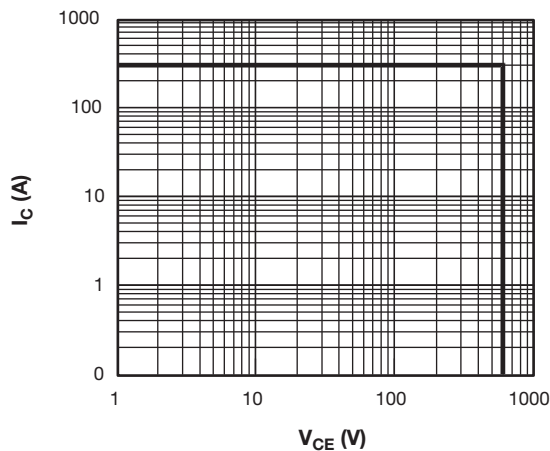
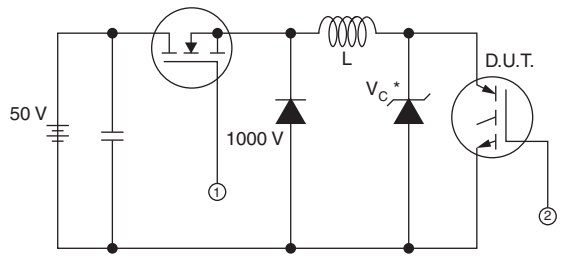
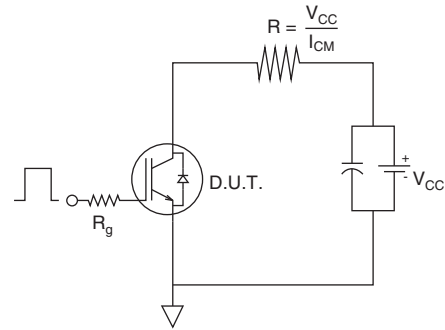


Fig. 18 - IGBT Reverse BIAS SOA, $T_J = 150\text{ }^\circ\text{C}$, $V_{GE} = 15\text{ V}$

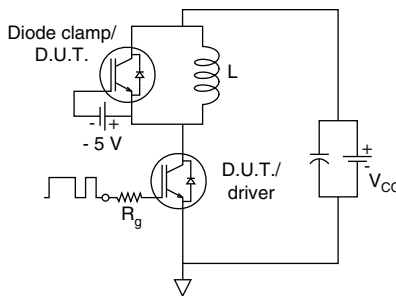


* Driver same type as D.U.T.; $V_C = 80\%$ of $V_{ce(max)}$
 * Note: Due to the 50 V power supply, pulse width and inductor will increase to obtain I_d

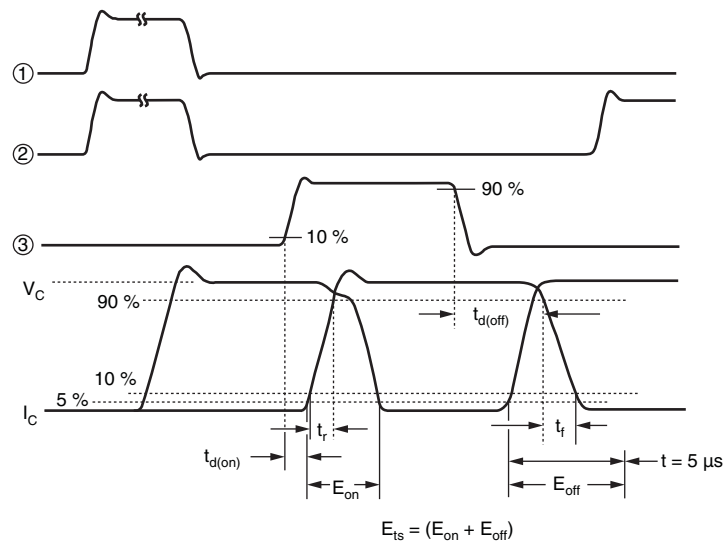
19a - Clamped Inductive Load Test Circuit



19b - Pulsed Collector Current Test Circuit



20a - Switching Loss Test Circuit



20b - Switching Loss Waveforms Test Circuit

ORDERING INFORMATION TABLE

Device code	VS-	G	B	90	D	A	60	U
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Vishay Semiconductors product
- 2** - Insulated Gate Bipolar Transistor (IGBT)
- 3** - B = IGBT Generation 5
- 4** - Current rating (90 = 90 A)
- 5** - Circuit configuration (D = Single switch with antiparallel diode)
- 6** - Package indicator (A = SOT-227)
- 7** - Voltage rating (60 = 600 V)
- 8** - Speed/type (U = Ultrafast IGBT)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
2 separate diodes, parallel pin-out	D	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425



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Material Category Policy

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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